

# High-Speed Pumping to UHV

Ko YAMAZAKI<sup>1</sup>, Junichi SHIKE<sup>1</sup>, Motoi YAMAGATA<sup>1</sup>, Masahiro KITANO<sup>1</sup>  
Michiru NISHIWAKI<sup>2</sup>, Shigeki KATO<sup>2</sup>

Kitano Seiki Co., Ltd<sup>1</sup>  
High Energy Accelerator Research Organization<sup>2</sup>

E-mail : yamazaki@kitano-seiki.co.jp

## Contents

Background  
Objective  
Experimental Details  
Results and Discussions  
Conclusions

## Background

Development of a high-speed pumping system for UHV yields to us

- Reduction of cost and waiting time for aiming experiment and production
- Reduction of power consumption
- Reduction of CO<sub>2</sub> emission which seriously influences global warming

It is well known that

- High-speed pumping is limited by water desorption from chamber surface
- The reduction of roughness of a vacuum surface is able to reduce outgassing from the surface

Main source of water vapor absorbed on chamber surface

- Atmosphere
- N<sub>2</sub> of purge gas

## Objective

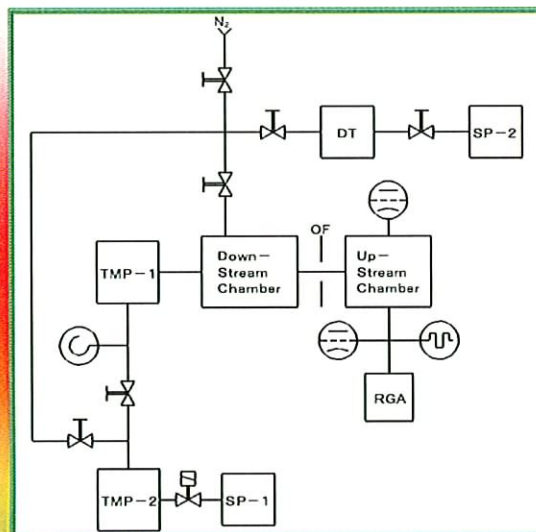
In this work, we aim quick pumping down to UHV without baking of system

- control of water vapor in a  $N_2$  gas purge line
- surface treatment of chambers
- measurement of outgassing rate and residual gas analysis

VASSCAA-4

KITANO SEIKI

## Setup of UHV System



DT : Dewpoint transducer  
SP : Dry scroll pump  
RGA : Residual gas analyzer  
OF: Orifice

VASSCAA-4

KITANO SEIKI



# Experimental Procedure

## Pumping Process

- Filled with nitrogen gas (4N) with 1atm at 1 hour
- The all pumps were suited on at same time

## Measurement of Outgassing Rate

- Orifice:  $5.2 \times 10^{-3} \text{ m}^3 \text{ s}^{-1}$ , 297 K
- Introduced gas: N<sub>2</sub> or Air (Pressure: N<sub>2</sub> equivalent)

VASSCAA-4

KITANO SEIKI

# Experimental Procedure

Surface roughness of the non-treated stainless steel

**RMS=7.1 $\mu\text{m}$**

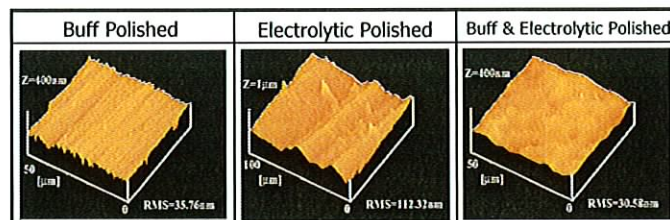


Treated with buff and electrolytic polished



**Improved**

**RMS=30.58 nm**



Surface Treatments

VASSCAA-4

KITANO SEIKI

## Water Vapor Concentration of Purge Gas

Purge gas	Purge Line	Water Concentration (vol. ppm)
Nitrogen	Stainless Steel Tube	0.065
Nitrogen		2.6
Nitrogen		12
Nitrogen	Polyurethane tube	160
Air	Stainless Steel Tube	12000

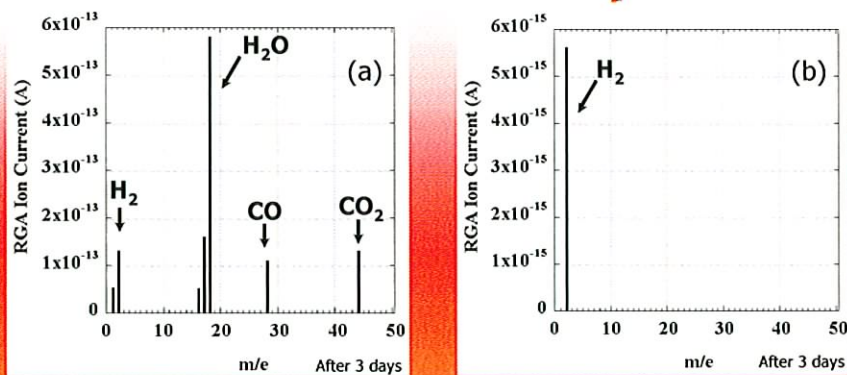
Water vapor concentration of purge gas is

- significantly influenced by product material of the gas purge line
- considerably reduced with baking of the purge line and N<sub>2</sub> gas flow rate in the line

VASSCAA-4

KITANO SEIKI

## Residual Gas Analysis



	(a)	(b)
Water Concentration	12000ppm in Air	0.065ppm in N <sub>2</sub> gas
Residual Gas Species	Water vapor	H <sub>2</sub> gas

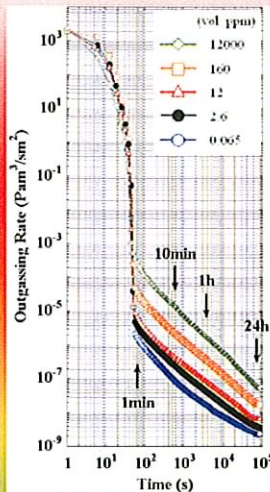
This quality of residual gas is equivalent to the quality in a baked UHV system

VASSCAA-4

KITANO SEIKI



## Outgassing Rate Influence of Water Concentration

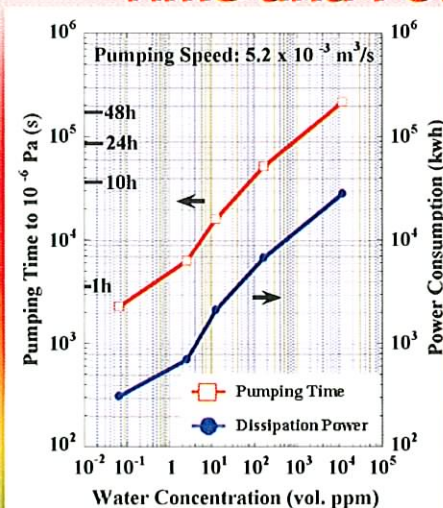


- Outgassing rates remarkably decreased with decreased of water vapor concentration of N<sub>2</sub> purge gas
- Water vapor from the purge gas had bad influence on the pumping time
- Outgassing rate of  $3 \times 10^{-9} \text{ Pam}^3\text{s}^{-1}\text{m}^{-2}$  was obtained without baking

VASSCAA-4

KITANO SEIKI

## Influence of Water Vapor on Pumping Time and Power Consumption



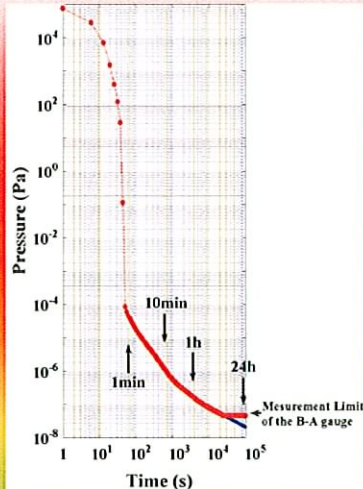
Water vapor in the purge gas	Reduction ratio of	
	Electrolytic Power	Pumping Time
0.065	1/100	1/90
2.6	1/35	1/40
12	1/15	1/15
160	1/20	1/4
12000	1	1

The pumping time to reach the pressure of  $1 \times 10^{-6} \text{ Pa}$  was also able to be shortened with two orders of the magnitude

VASSCAA-4

KITANO SEIKI

## Quick Pumping Without Under Control of Water Vapor



Pumping down without orifice after exposure  
N<sub>2</sub> gas with water vapor of 0.11vol. ppm

**A pressure of  $3 \times 10^{-8}$  Pa  
was obtained after 24 hours**

VASSCAA-4

KITANO SEIKI

## Conclusion

- We carried out control of water vapor in a N<sub>2</sub> gas purge line in addition to surface treatments of chambers.
- It was found that the main residual gas in the chamber without baking was H<sub>2</sub> after pumping down with the low concentration of water vapor. This quality of residual gas is equivalent to the quality in a baked UHV system.
- The introduction of well controlled N<sub>2</sub> gas to the vacuum system which was not baked out has proved a pressure of  $3 \times 10^{-8}$  Pa for 24 hours in the chamber without orifice. The pumping time to reach the pressure of  $1 \times 10^{-6}$  Pa was also able to be shortened with two orders of the magnitude.
- High-speed pumping demonstrated in this study should considerably contribute to reduce waiting time before vacuum work and electrical power consumption, namely, CO<sub>2</sub> emission which seriously influences global warming

VASSCAA-4

KITANO SEIKI